

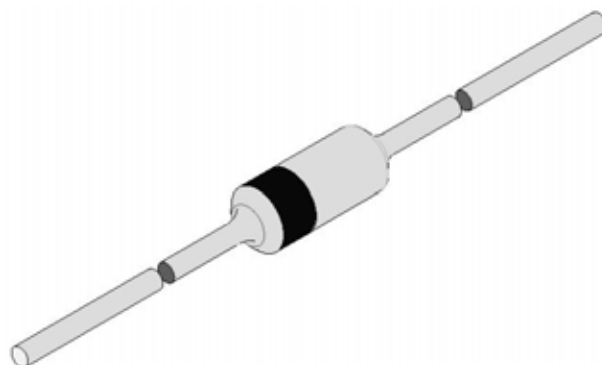
# Schottky Barrier Diode

## Features

1. High reliability
2. Low reverse current and low forward voltage

## Applications

Low current rectification and high speed switching



## Construction

Silicon epitaxial planar

## Absolute Maximum Ratings

$T_j=25$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	$V_{RRM}$	40	V
		1N60P	$V_{RRM}$	45	V
Peak forward surge current	$t_p$ 1 s	1N60	$I_{FSM}$	150	mA
		1N60P	$I_{FSM}$	500	mA
Forward continuous current	$T_a=25$	1N60	$I_F$	30	mA
		1N60P	$I_F$	50	mA
Storage temperature range			$T_{stg}$	-65~+125	

## Maximum Thermal Resistance

$T_j=25$

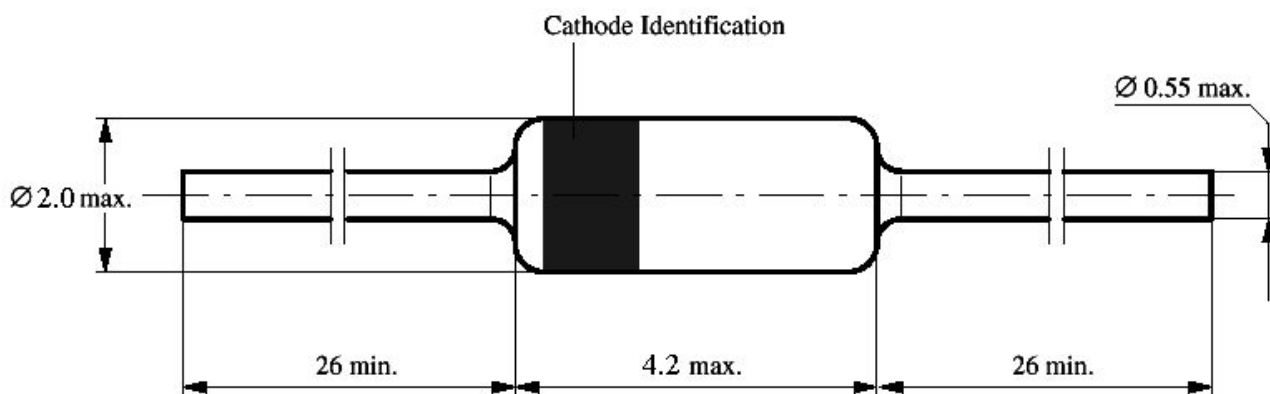
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm x 50mm x 1.6mm	$R_{thJA}$	250	K/W

## Electrical Characteristics

$T_j=25$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	1N60	$V_F$		0.32	0.5	V
		1N60P	$V_F$		0.24	0.5	V
	$I_F=30\text{mA}$	1N60	$V_F$		0.65	1.0	V
	$I_F=200\text{mA}$	1N60P	$V_F$		0.65	1.0	V
Reverse current	$V_R=15\text{V}$	1N60	$I_R$		0.1	0.5	$\mu\text{A}$
		1N60P	$I_R$		0.5	1.0	$\mu\text{A}$
Junction capacitance	$V_R=1\text{V}$ , $f=1\text{MHz}$	1N60	$C_J$		2.0		pF
	$V_R=10\text{V}$ , $f=1\text{MHz}$	1N60P	$C_J$		6.0		pF
Reverse recovery time	$I_F=I_R=1\text{mA}$ $I_{tr}=1\text{mA}$ $R_C=100\Omega$		$t_{rr}$			1.0	ns

## Dimensions in mm



Standard Glass Case  
JEDEC DO 35

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